

PMEG3050EP

5 A low V_F MEGA Schottky barrier rectifier Rev. 01 — 10 December 2009

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Average forward current: I_{F(AV)} ≤ 5 A
- Reverse voltage: V_R ≤ 30 V
- Low forward voltage
- High power capability due to clip-bond technology
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Quick reference data $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	square wave; $\delta = 0.5$; f = 20 kHz				
		$T_{amb} \le 35 ^{\circ}C$	[1] -	-	5	Α
		$T_{sp} \le 130 ^{\circ}C$	-	-	5	Α
V_R	reverse voltage		-	-	30	V
V_{F}	forward voltage	I _F = 5 A	-	315	360	mV
I _R	reverse current	$V_R = 30 V$	-	2.6	8	mA

^[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	
2	anode	1 2	1 - 2
		<u> </u>	sym001

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG3050EP	-	plastic surface-mounted package; 2 leads	SOD128

4. Marking

Table 4. Marking codes

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Type number	Marking code
PMEG3050EP	A7

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage	$T_j = 25 ^{\circ}C$	-	30	V
I _{F(AV)}	average forward current	square wave; δ = 0.5; f = 20 kHz			
		$T_{amb} \leq 35 ^{\circ}C$	<u>[1]</u> -	5	Α
		$T_{sp} \le 130 ^{\circ}C$	-	5	Α
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	[2] _	70	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[3][4]	625	mW
			[3][5]	1050	mW
			[3][1]	2100	mW

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T_j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [2] $T_i = 25$ °C prior to surge.
- [3] Reflow soldering is the only recommended soldering method.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

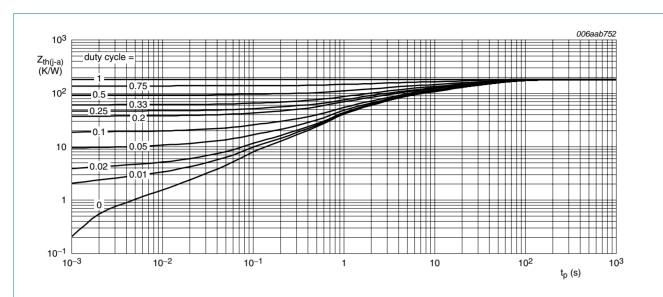
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance junction to ambient	thermal resistance from	in free air	[1][2]			
	junction to ambient		[3]	-	200	K/W
			<u>[4]</u> _	-	120	K/W
			<u>[5]</u> _	-	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[6]</u> _	-	12	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [6] Soldering point of cathode tab.

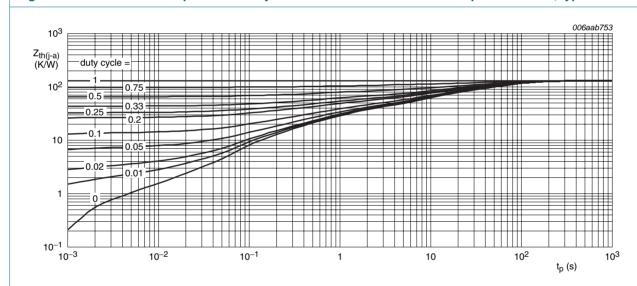
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FR4 PCB, standard footprint

Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

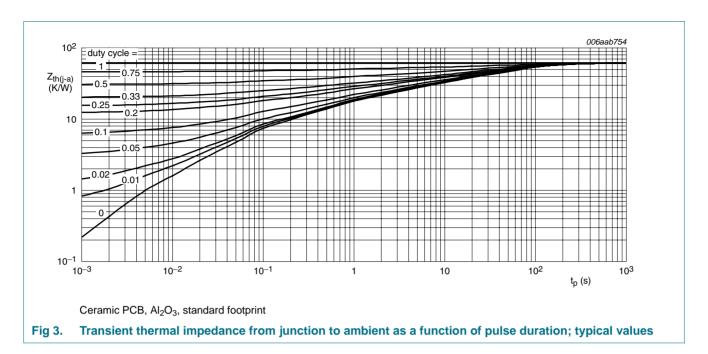


FR4 PCB, mounting pad for cathode 1 cm²

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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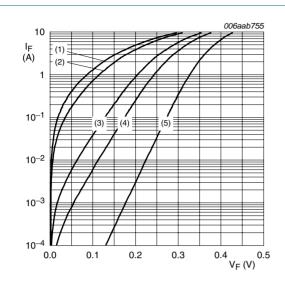


Characteristics 7.

Table 7. **Characteristics**

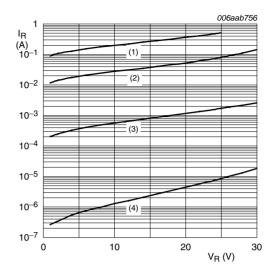
 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	I _F = 1 A	-	240	275	mV
		I _F = 3 A	-	285	340	mV
		I _F = 5 A	-	315	360	mV
I _R reverse current	reverse current	$V_R = 5 V$	-	330	-	μΑ
		$V_R = 30 \text{ V}$	-	2.6	8	mA
C_d	diode capacitance	f = 1 MHz				
		$V_R = 1 V$	-	800	-	pF
		V _R = 10 V	-	260	-	pF



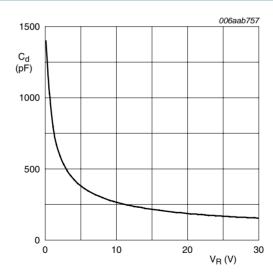
- (1) $T_i = 150 \, ^{\circ}\text{C}$
- (2) $T_i = 125 \, ^{\circ}\text{C}$
- (3) $T_i = 85 \, ^{\circ}C$
- (4) $T_i = 25 \, ^{\circ}C$
- (5) $T_i = -40 \, ^{\circ}\text{C}$

Forward current as a function of forward Fig 4. voltage; typical values



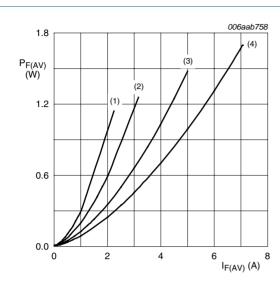
- (1) $T_i = 125 \, ^{\circ}C$
- (2) $T_i = 85 \, ^{\circ}C$
- (3) $T_j = 25 \, ^{\circ}C$
- (4) $T_i = -40 \, ^{\circ}\text{C}$

Reverse current as a function of reverse Fig 5. voltage; typical values



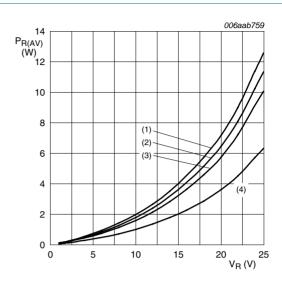
 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$

Diode capacitance as a function of reverse voltage; typical values Fig 6.



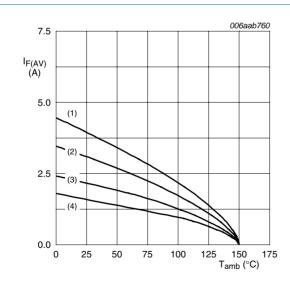
- (1) $\delta = 0.1$
- (2) $\delta = 0.2$
- (3) $\delta = 0.5$
- (4) $\delta = 1$

Fig 7. Average forward power dissipation as a function of average forward current; typical values



- (1) $\delta = 1$
- (2) $\delta = 0.9$
- (3) $\delta = 0.8$
- (4) $\delta = 0.5$

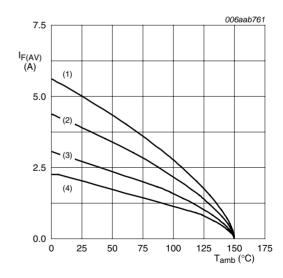
Fig 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

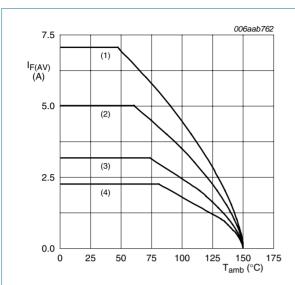
Fig 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

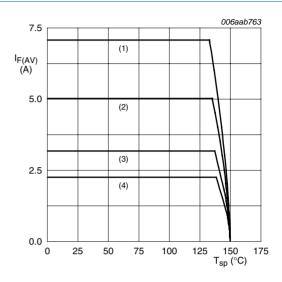
Fig 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

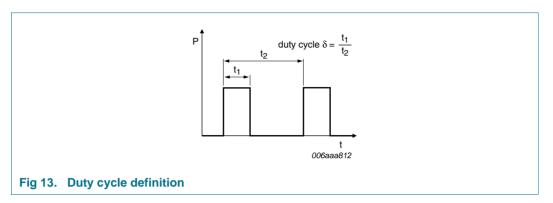
Fig 11. Average forward current as a function of ambient temperature; typical values



- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Fig 12. Average forward current as a function of solder point temperature; typical values

8. Test information

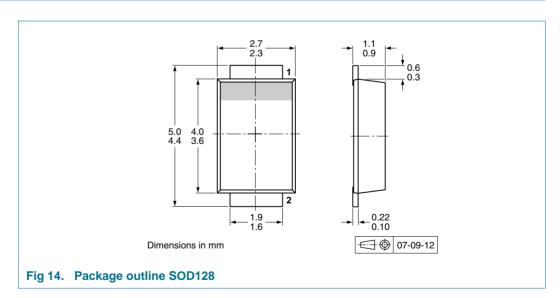


The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



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10. Packing information

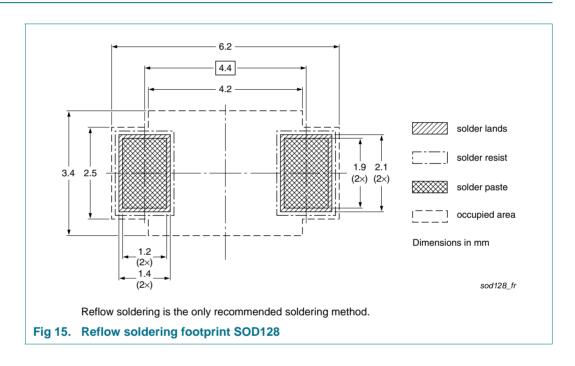
Table 8. **Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity 3000
	005.150		1111
PMEG3050EP	SOD128	4 mm pitch, 12 mm tape and reel	-115

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



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12. Revision history

Table 9. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3050EP_1	20091210	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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